

#### **Features**

- · Split Gate Trench MOSFET Technology
- · Low Thermal Resistance
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

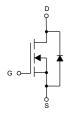
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 40°C/W Junction to Ambient (Note 2)
- Thermal Resistance: 0.4°C/W Junction to Case

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V <sub>DS</sub>	100	V	
Gate-Source Volltage		$V_{GS}$	±20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	- I <sub>D</sub>	220	Α	
	T <sub>C</sub> =100°C	- 'D	155		
Pulsed Drain Current (Note 3)		I <sub>DM</sub>	880	Α	
Total Power Dissipation (Note 4)		P <sub>D</sub>	375	W	
Single Pulsed Avalanche Energy <sup>(Note 5)</sup>		E <sub>AS</sub>	902	mJ	

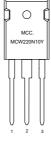
#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of  $R_{\theta,JA}$  is measured with the device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$  =25°C.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P<sub>D</sub> is based on max. junction temperature, using junction-case thermal resistance.
- 5.  $T_J$ =25°C,  $V_{DD}$ =50V,  $V_{GS}$ =10V, L=5mH.

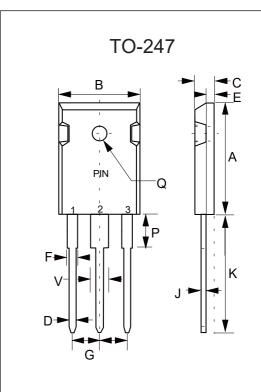
# **Internal Structure and Marking Code**



- 1. Gate
- Drain
  Source



# N-CHANNEL MOSFET



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	NOIL
Α	0.787	0.866	20.00	22.00	
В	0.598	0.638	15.20	16.20	
С	0.185	0.208	4.70	5.30	
D	0.035	0.059	0.90	1.50	
Е	0.059	0.094	1.50	2.40	
F	0.067	0.091	1.70	2.30	
J	0.019	0.031	0.48	0.80	
K	0.748	0.833	19.00	21.15	
Р	0.122	0.189	3.10	4.80	
Q	0.118	0.150	3.00	3.80	Ф
V	0.106	0.134	2.70	3.40	
G	0.197	0.224	5.00	5.70	

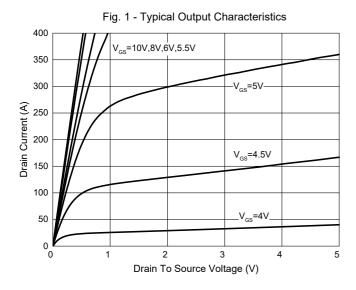


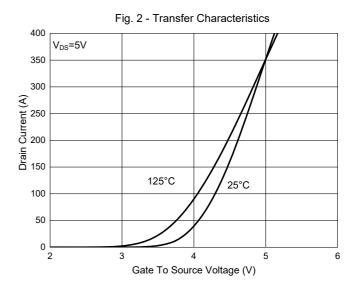
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

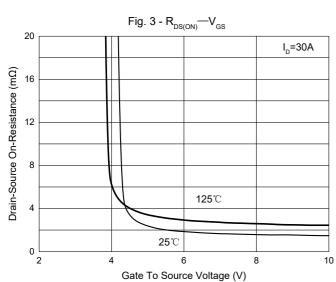
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =1mA	100			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2	2.5	4	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A		1.8	2.4	mΩ	
Gate Resistance	R <sub>g</sub>	f=1MHz,Open drain		1.2		Ω	
Diode Characteristics							
Continuous Body Diode Current	Is				220	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =30A			1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	V =0V I =20A		120		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$V_{GS}$ =0V, $I_{S}$ =30A		404		nC	
Dynamic Characteristics							
Input Capacitance	C <sub>iss</sub>			10051		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =50V, $V_{GS}$ =0V,f=100KHz		2015			
Reverse Transfer Capacitance	C <sub>rss</sub>			30			
Total Gate Charge	Q <sub>g</sub>			166			
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =50V, $V_{GS}$ =10V, $I_{D}$ =30A		34		nC	
Gate-Drain Charge	$Q_{gd}$			49			
Turn-On Delay Time	t <sub>d(on)</sub>			30			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V,		65		- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=4.5\Omega$ , $I_{DS}=30A$		121			
Turn-Off Fall Time	t <sub>f</sub>			107			

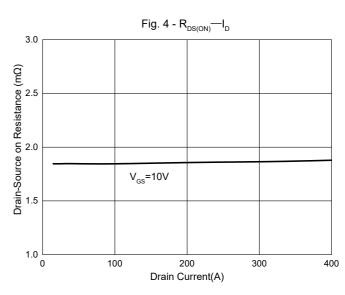


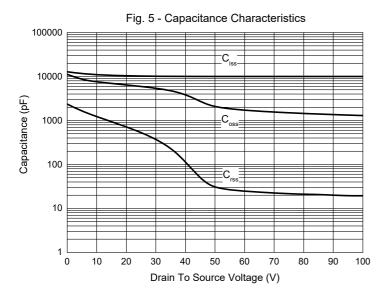
#### **Curve Characteristics**

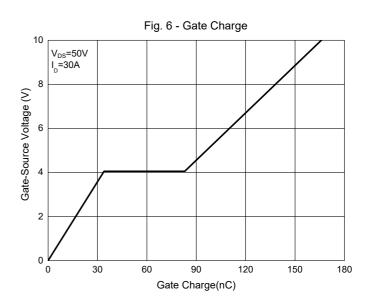






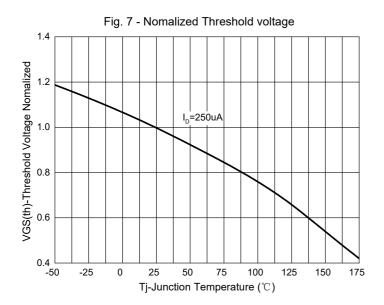


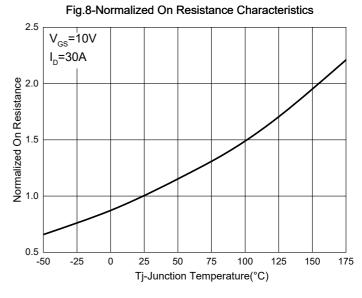


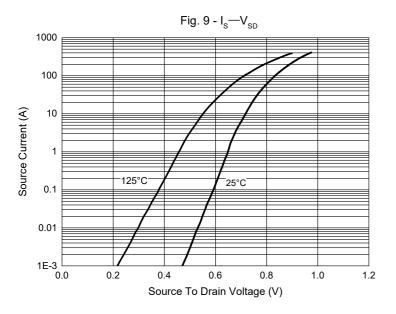


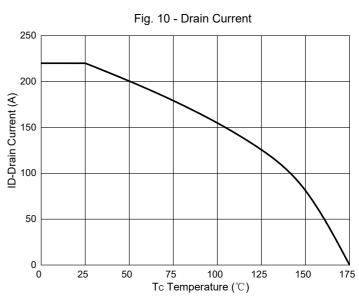


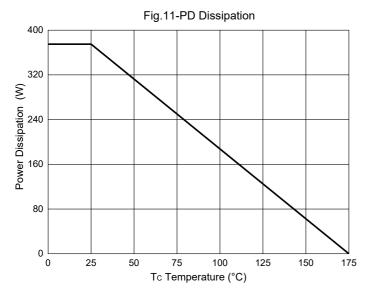
### **Curve Characteristics**













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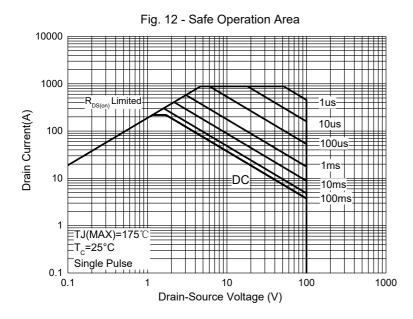
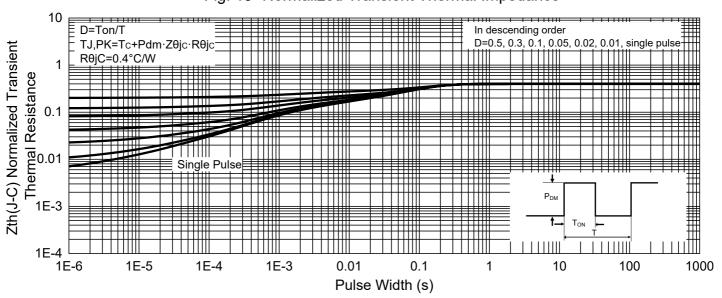


Fig. 13 -Normalized Transient Thermal Impedance





## **Ordering Information**

Device	Packing		
Part Number-BP	Tube:30pcs/Tube, 360pcs/Box,1.8K/Ctn;		

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